

Absolute Maximum Ratings at $T_j=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	600	V
Gate-source voltage	V_{GS}	± 30	V
Continuous drain current ¹⁾ , $T_C=25^\circ\text{C}$	I_D	8	A
Continuous drain current ¹⁾ , $T_C=100^\circ\text{C}$		5	
Pulsed drain current ²⁾ , $T_C=25^\circ\text{C}$	$I_{D, \text{pulse}}$	24	A
Continuous diode forward current ¹⁾ , $T_C=25^\circ\text{C}$	I_S	8	A
Diode pulsed current ²⁾ , $T_C=25^\circ\text{C}$	$I_{S, \text{pulse}}$	24	A
Power dissipation ³⁾ , $T_C=25^\circ\text{C}$	P_D	63	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	150	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0\ldots 480\text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0\ldots 480\text{ V}$, $I_{SD} = I_D$	dv/dt	15	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	R_{JC}	2	$^\circ\text{C}/\text{W}$
Thermal resistance, junction-ambient ⁴⁾	R_{JA}	62	$^\circ\text{C}/\text{W}$

Electrical Characteristics at $T_j=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	600			V	$V_{GS}=0\text{ V}$, $I_D=250\text{ }\mu\text{A}$
		650	716			$V_{GS}=0\text{ V}$, $I_D=250\text{ }\mu\text{A}$, $T_j=150^\circ\text{C}$
Gate threshold voltage	$V_{GS(\text{th})}$	2.0		4.0	V	$V_{DS}=V_{GS}$, $I_D=250\text{ }\mu\text{A}$
Drain-source on-state resistance	$R_{DS(\text{ON})}$		0.50 1.27	0.58		$V_{GS}=10\text{ V}$, $I_D=4\text{ A}$ $V_{GS}=10\text{ V}$, $I_D=4\text{ A}$, $T_j=150^\circ\text{C}$

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C _{iss}		464		pF	V _{GS} =0 V, V _{DS} =50 V, f=1 MHz
Output capacitance	C _{oss}		38.3		pF	
Reverse transfer capacitance	C _{rss}		1.47		pF	

Turn-

Electrical Characteristics Diagrams

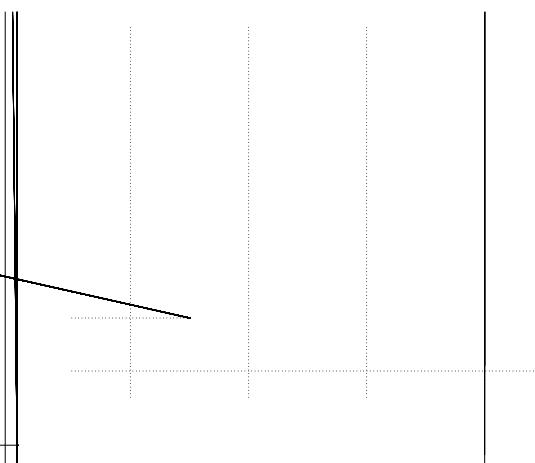


Figure 1. Typ. output characteristics

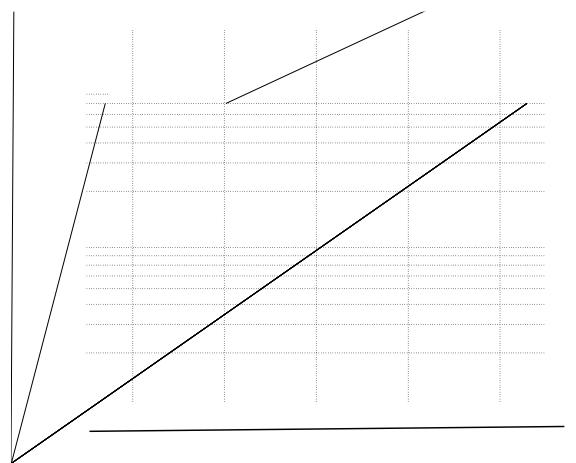


Figure 2. Typ. transfer characteristics

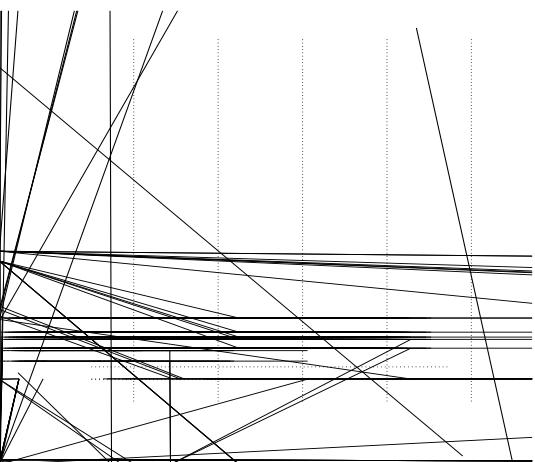


Figure 3. Typ. capacitances

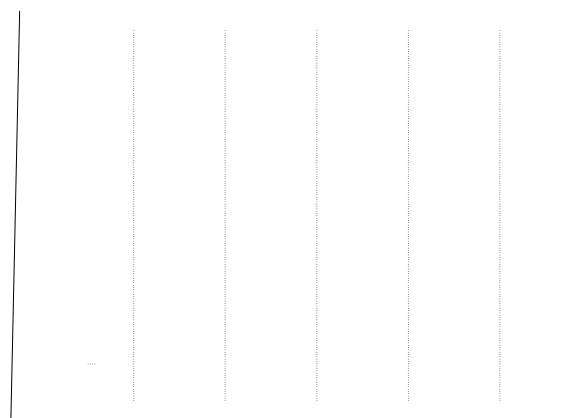


Figure 4. Typ. gate charge

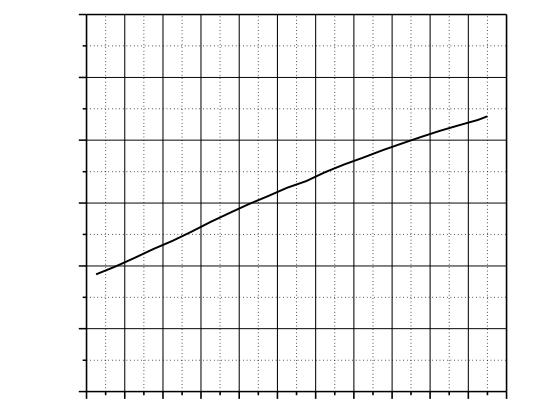


Figure 5. Drain-source breakdown voltage

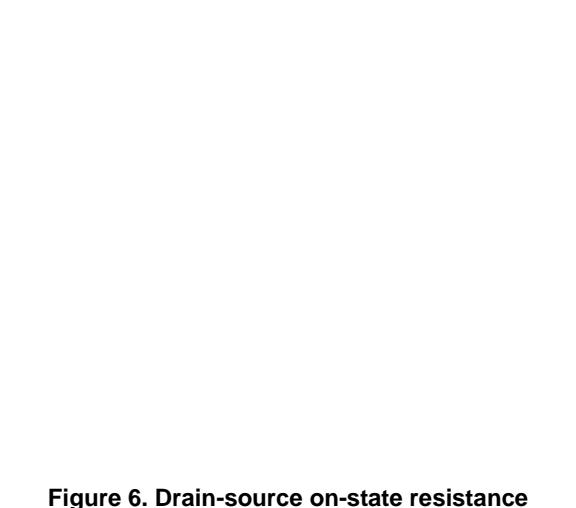


Figure 6. Drain-source on-state resistance

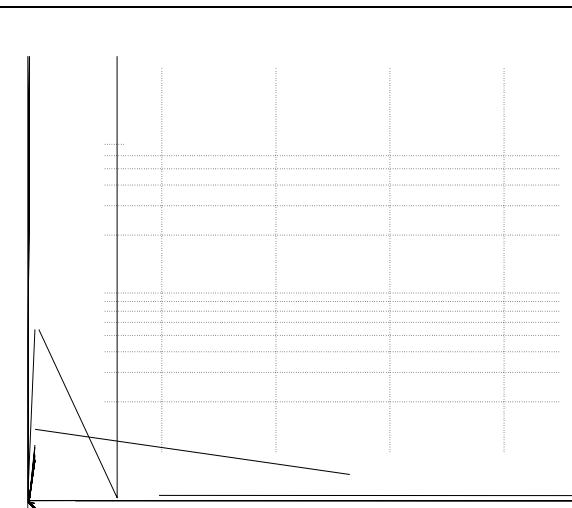


Figure 7. Forward characteristic of body diode

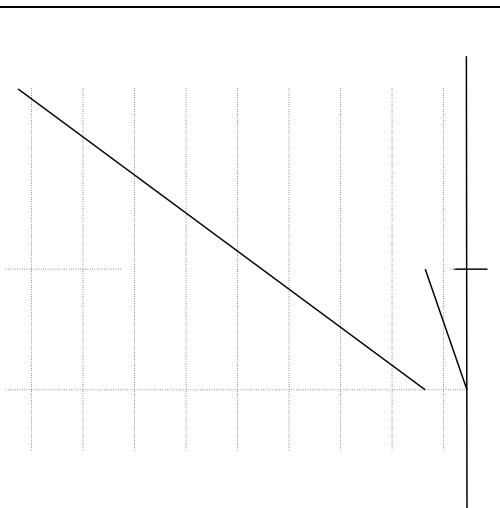


Figure 8. Drain-source on-state resistance

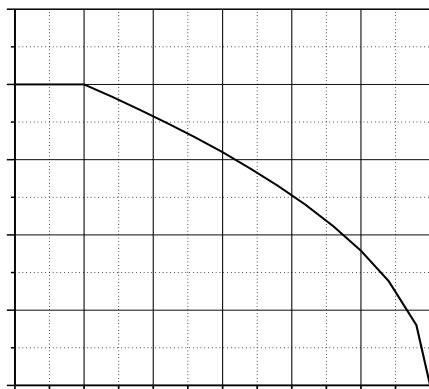


Figure 9. Drain current

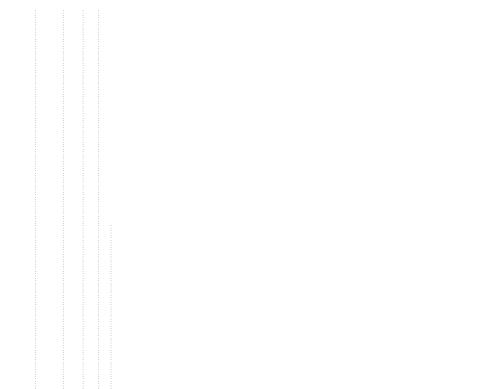
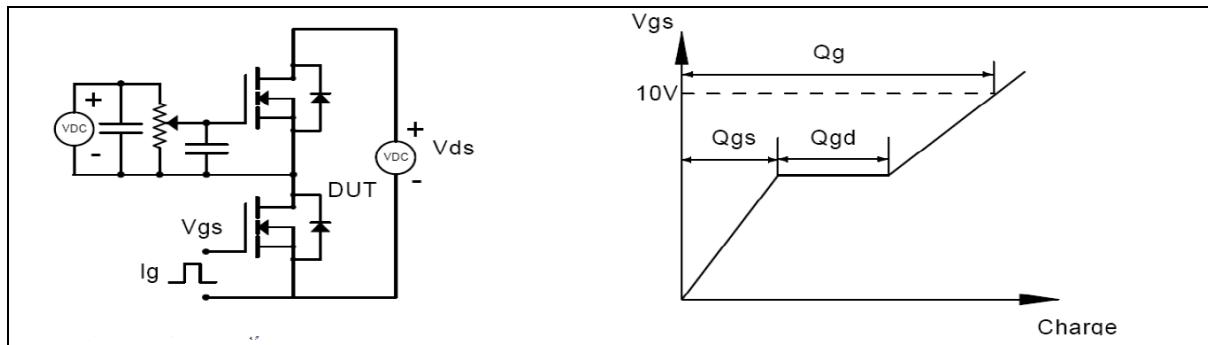
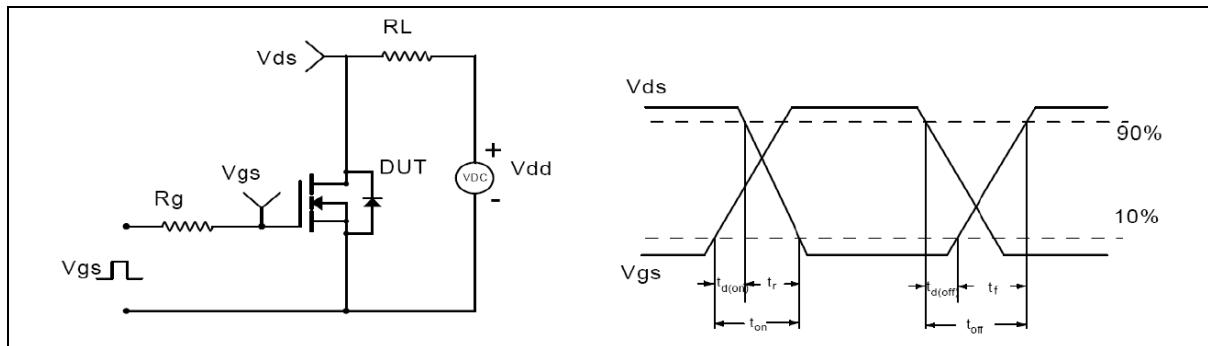
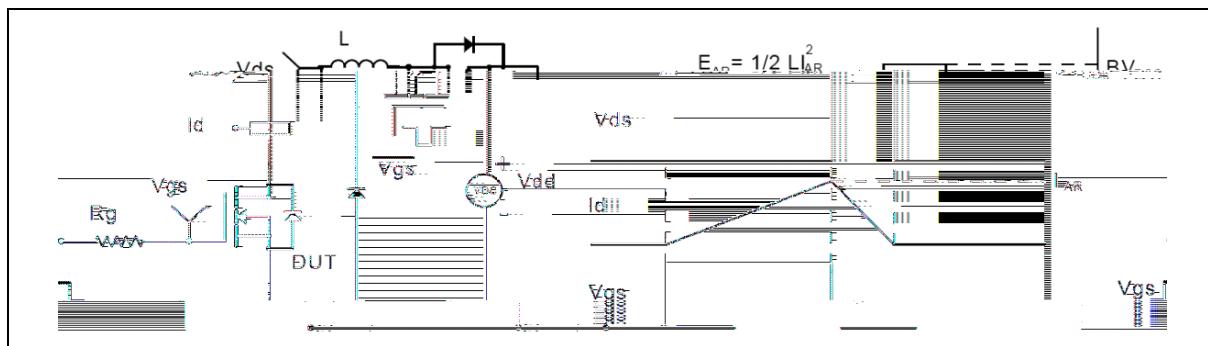
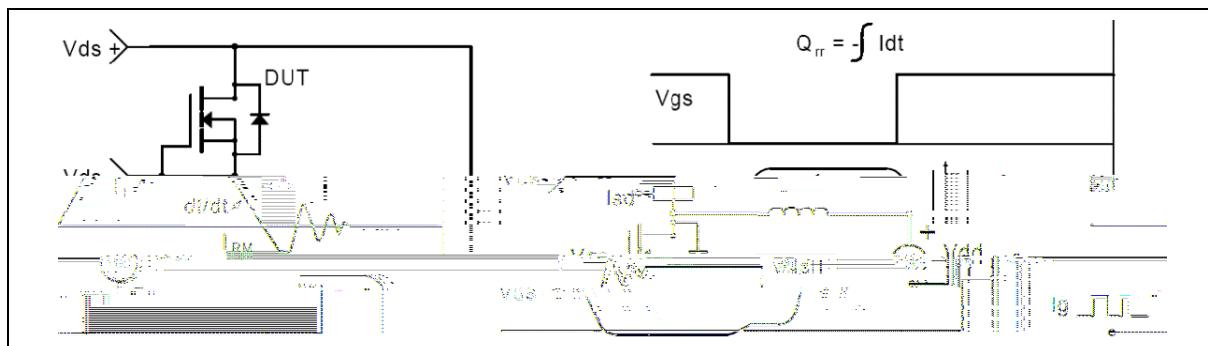
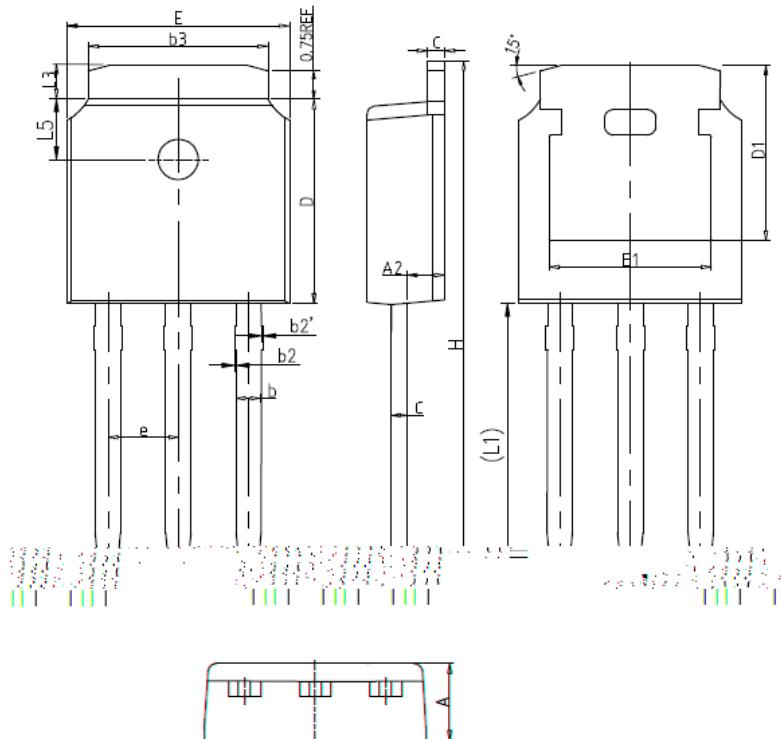


Figure 10. Safe operation area $T_c=25^\circ\text{C}$

Test circuits and waveforms

Figure 1. Gate charge test circuit & waveform

Figure 2. Switching time test circuit & waveforms

Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm		
	Min	Nom	Max
A	2.20	2.30	2.40
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b2	0.00	0.04	0.10
b2'	0.00	0.04	0.10
b3	5.20	5.33	5.50
c	0.43	0.53	0.63
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.80
E1	4.63	-	-
e	2.286BSC		
H	16.22	16.52	16.82
L1	9.15	9.40	9.65
L3	0.88	1.02	1.28
L5	1.65	1.80	1.95

Version1: TO251-C package outline dimension

Ordering Information

Package Type	Units/ Tube	Tubes / Inner Box	Units/ Inner Box	Inner Box/ Carton Box	Units/ Carton Box
TO251-C	75	66	4950	6	29700

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG60R580AF	TO251	yes	yes	yes

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